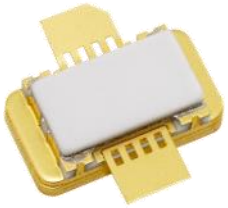
■ Features

- High Voltage Operation : V_{DS}=50V
- High Power : 54.0dBm (typ.) @ Psat
- Proven Reliability



■ Description

Sumitomo Electric's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power L-band amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use from 2.65GHz W-CDMA & LTE design requirements as it offers high gain, long term reliability and ease of use.

ABSOLUTE MAXIMUM RATINGS (Case Temperature Tc=25deg.C)

Item	Symbol	Condition	Rating	Unit
Operating-Voltage	V_{DS}		55	V
Drain-Source Voltage	V_{DS}	V_{GS}=-8V	160	V
Gate-Source Voltage	V_{GS}		-15	V
Total Power Dissipation	P_t		160.7	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	V_{DS}		$\leq$ 55	V
Forward Gate Current	I_{GF}	R_G=5 ohm	$\leq$ 189	mA
Reverse Gate Current	I_{GR}	R_G=5 ohm	$\geq$ -6.9	mA
Channel Temperature	T_{ch}		$\leq$ 200	deg.C
Average Output Power	$P_{ave.}$		$\leq$ 51.0	dBm

ELECTRICAL CHARACTERISTICS (Case Temperature T_c=25deg.C)

Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-Off Voltage	V_p	V_{DS}=50V I_{DS}=48mA	-4.0	-	-2.0	V
Saturated Power	Psat *1	V_{DS}=50V $I_{DS(DC)}$=0mA f=2.65GHz	53.0	54.0	-	dBm
Drain Eficiency at Psat	DE *1		50	57	-	%
Power Gain	Gp *2	$I_{DS(DC)}$=800mA	14.0	15.0	-	dB
Thermal Resistance	R_{th}	Channel to Case at 105W P_{DC}	-	1.2	1.4	deg.C/W

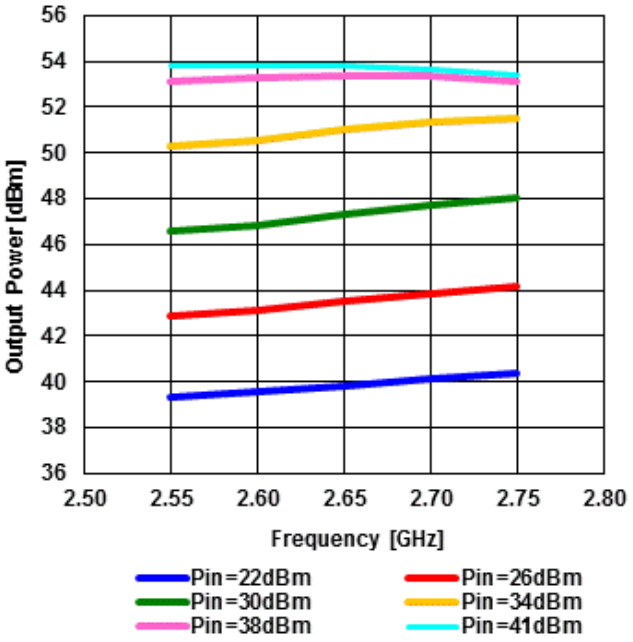
*1 : Pin=41dBm 10%-duty RF pulse (DC supply constant)

*2 : Pout=46dBm, CW modulation Signal (W-CDMA)

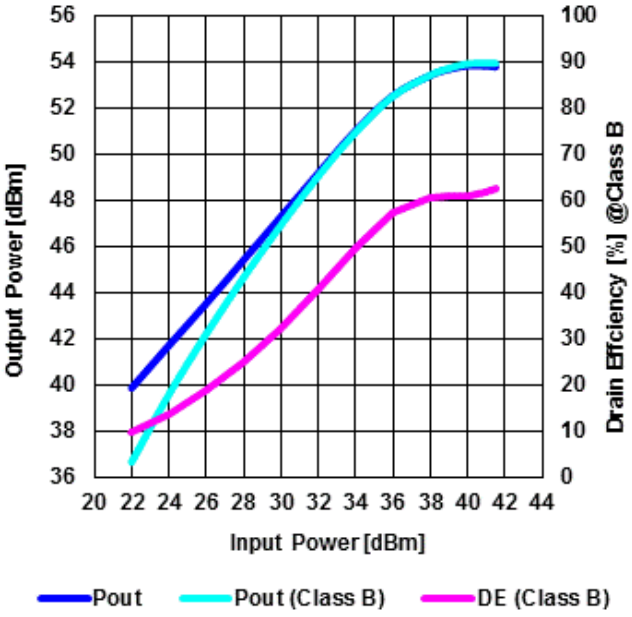
RoHS Compliance	YES

RF characteristics @ f=2.65GHz fine tuned

Output Power vs. Frequency
V_{DS}=50V $I_{DS(DC)}$=900mA

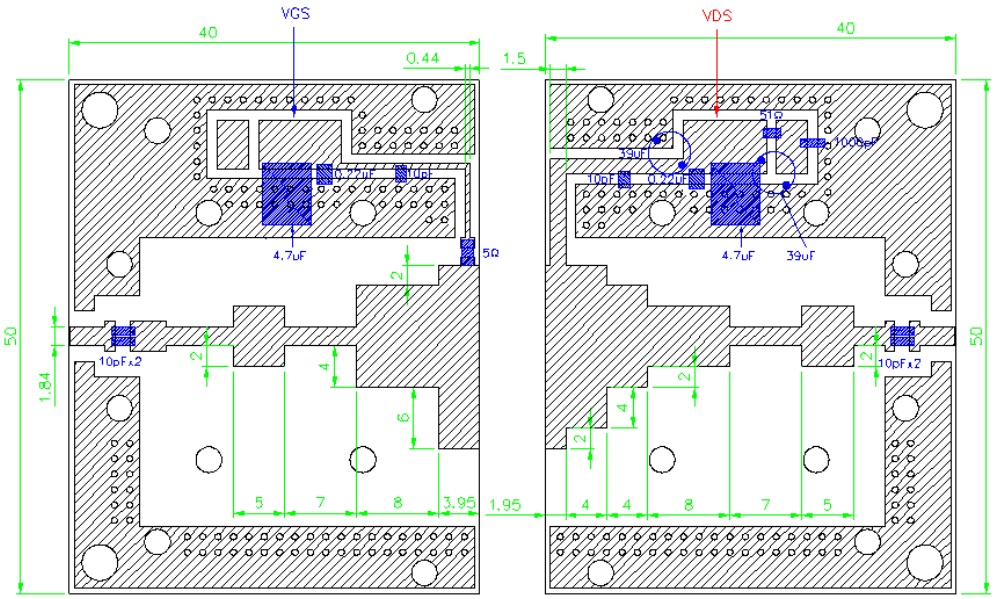


Output Power and Drain Efficiency vs. Input Power
V_{DS}=50V $I_{DS(DC)}$=900mA f=2.65GHz



Pulse Signal (10%-duty, DC : constant)

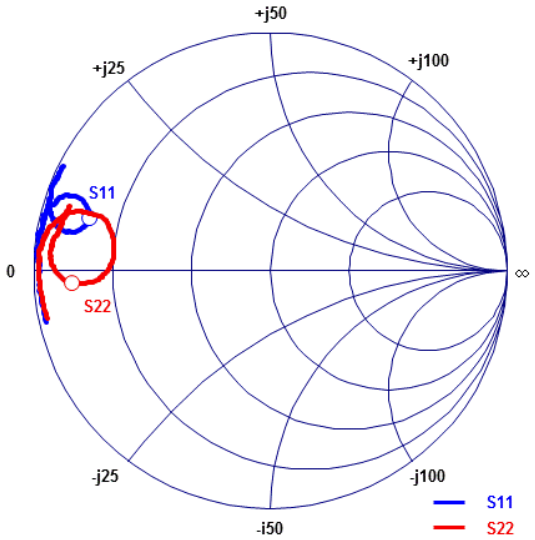
Test Fixture

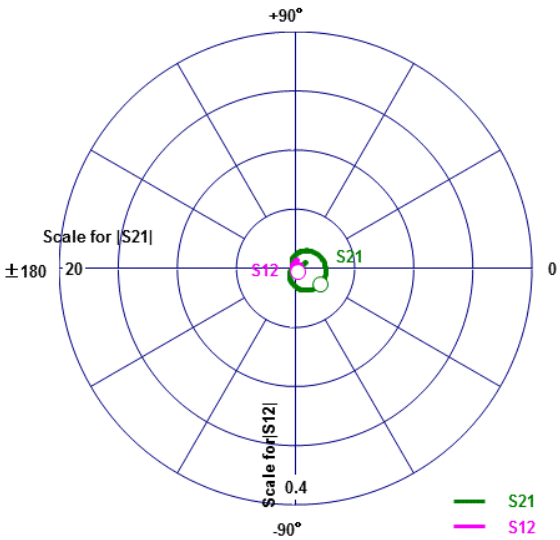


h=0.8mm εr=3.5
Cu=18um Unit: mm

- Reference DATA -

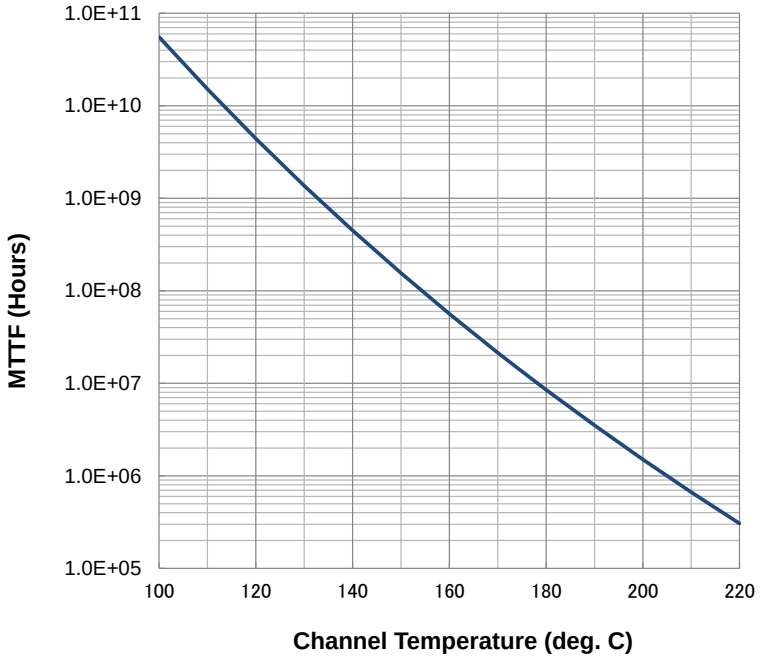
S-Parameters @V_{DS}=50V, $I_{DS(DC)}$=900mA, f=0.5 to 4.5GHz
Zl = Zs = 50 ohm Marker : 2.65GHz





Freq.	S11		S21		S12		S22	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.5	0.97	-167.18	0.99	30.19	0.001	-14.25	0.97	-167.97
0.6	0.98	-174.57	0.60	21.99	0.001	24.29	0.97	-174.67
0.7	0.98	178.51	0.35	17.54	0.001	29.79	0.98	178.80
0.8	0.98	177.49	0.19	28.07	0.001	80.22	0.98	177.20
0.9	0.98	176.31	0.10	65.74	0.002	78.01	0.98	175.66
1.0	0.98	175.43	0.13	113.20	0.002	82.62	0.98	174.56
1.1	0.99	174.72	0.21	129.04	0.002	79.97	0.97	172.94
1.2	0.98	173.76	0.28	132.07	0.003	78.74	0.97	171.50
1.3	0.98	172.47	0.37	130.37	0.004	83.15	0.96	170.15
1.4	0.99	171.72	0.46	126.65	0.004	76.30	0.95	168.77
1.5	0.99	170.99	0.55	122.48	0.004	74.10	0.93	167.52
1.6	0.98	169.77	0.65	117.38	0.005	76.26	0.91	165.84
1.7	0.98	168.52	0.76	109.75	0.006	70.68	0.89	164.49
1.8	0.99	167.33	0.90	102.39	0.006	67.47	0.87	163.42
1.9	0.99	166.85	1.08	93.75	0.007	63.01	0.84	162.60
2.0	0.98	165.13	1.27	84.01	0.008	57.10	0.80	162.56
2.1	0.97	163.84	1.48	72.32	0.009	46.39	0.74	162.55
2.2	0.95	162.32	1.75	58.49	0.009	36.01	0.70	165.39
2.3	0.93	160.64	2.01	42.93	0.010	23.86	0.67	169.68
2.4	0.90	159.58	2.32	25.35	0.010	6.16	0.67	175.46
2.5	0.85	159.61	2.54	3.83	0.010	-17.43	0.71	-178.46
2.6	0.81	162.02	2.58	-19.61	0.008	-44.08	0.79	-176.17
2.7	0.80	165.61	2.44	-42.93	0.007	-76.74	0.88	-177.72
2.8	0.82	168.00	2.10	-64.21	0.005	-114.53	0.92	178.69
2.9	0.86	169.12	1.75	-81.78	0.005	-154.23	0.93	176.04
3.0	0.90	169.08	1.43	-96.14	0.005	174.09	0.93	173.72
3.1	0.93	168.17	1.18	-108.04	0.005	153.36	0.93	172.07
3.2	0.94	167.11	0.98	-118.10	0.006	135.06	0.92	171.06
3.3	0.95	166.03	0.82	-126.62	0.007	122.49	0.91	170.36
3.4	0.97	164.92	0.70	-134.36	0.007	115.81	0.91	169.93
3.5	0.98	163.84	0.60	-140.76	0.008	110.54	0.91	169.10
3.6	0.98	162.64	0.53	-146.73	0.009	105.35	0.91	168.20
3.7	0.98	161.65	0.46	-152.73	0.009	101.71	0.90	167.94
3.8	0.98	160.45	0.41	-157.75	0.009	97.02	0.90	167.28
3.9	0.99	159.42	0.37	-162.71	0.010	93.63	0.90	166.53
4.0	0.99	158.32	0.33	-167.57	0.010	92.40	0.90	165.70
4.1	0.99	157.57	0.30	-171.91	0.011	90.68	0.90	164.98
4.2	0.98	156.54	0.27	-176.45	0.012	89.87	0.90	164.69
4.3	0.98	155.17	0.25	179.35	0.013	85.26	0.90	163.65
4.4	0.98	154.33	0.23	174.60	0.014	81.85	0.89	162.86
4.5	0.98	153.35	0.21	171.07	0.015	79.42	0.89	162.13

MTTF Calculation
– Estimated MTTF –



Ea=1.6eV
Confidence Level=90%

Channel Temp (deg.C)	MTTF (Hours)
160	5.98×10^7
180	9.02×10^6
200	1.60×10^6

$AF=\exp[(-Ea/k)(1/T_{stress}-1/T_{use})$

$MTTF_{use}=MTTF_{stress}*AF$

Where;

AF: acceleration factor

Ea: activation energy (1.6 eV)

k: Boltzman's constant (8.62×10^{-5} eV/K)

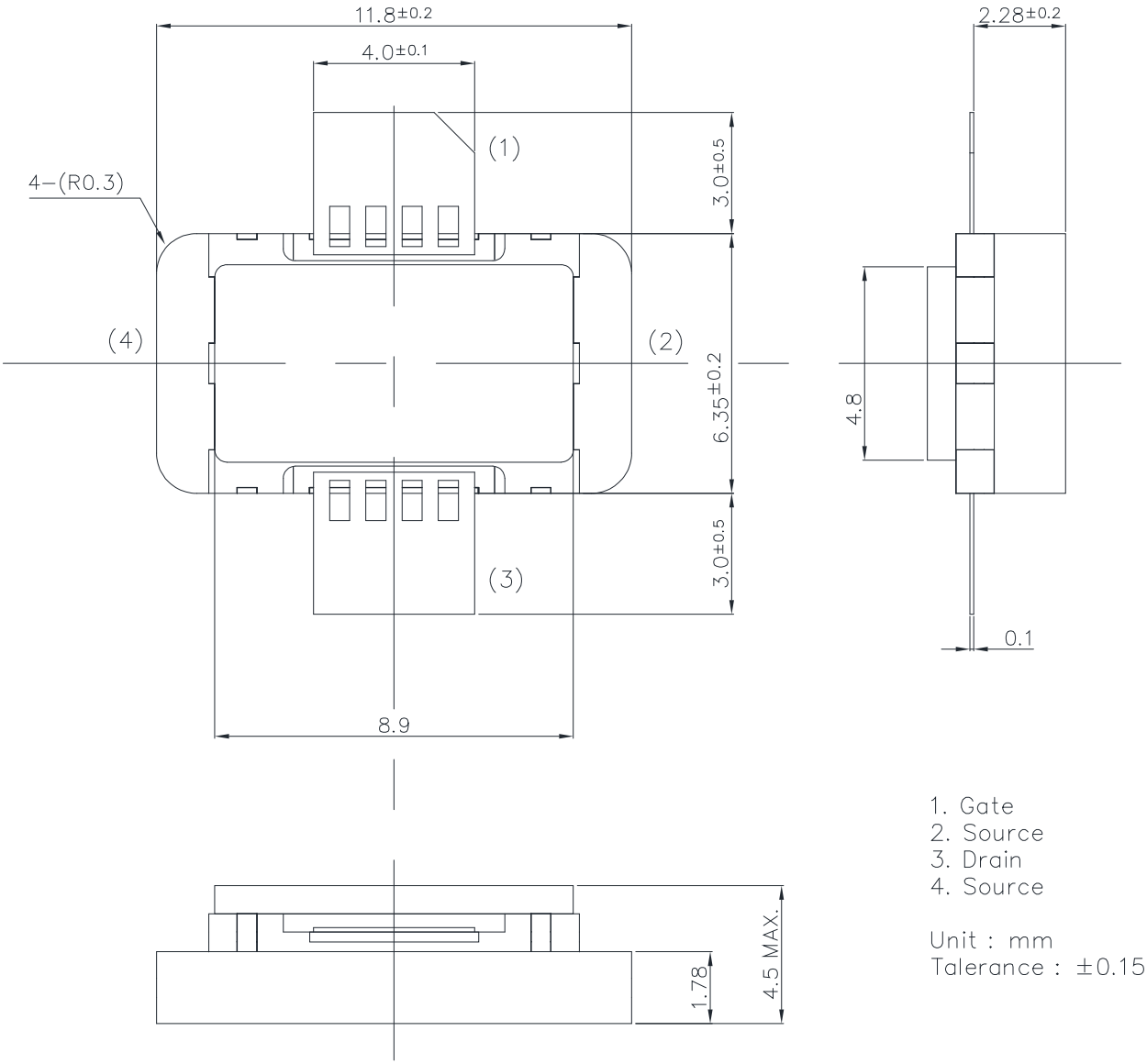
T_{stress}: stress temperature (K)

T_{use}: use temperature (K)

ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	1B
Machine Model (per JEIA/ESD22-A115)	A
Device Charged Model (per JESD22-C101)	IV

M1H Package Outline
Metal-Ceramic Hermetic Package



1. Gate
2. Source
3. Drain
4. Source

Unit : mm
Talerance : ±0.15

For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
  This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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